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Vishay Siliconix

N-Channel 40 V (D-S) MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00342				
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00478				
Q _g typ. (nC)	14.8				
I _D (A)	96				
Configuration	Single				

FEATURES

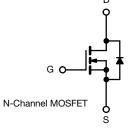
- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R_{DS}-Q_{oss} FOM
- 100 % Rq and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics





APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- DC/AC inverters
- · Battery and load switch



ORDERING INFORMATION							
Package PowerPAK SO-8L							
Lead (Pb)-free and halogen-free	ree and halogen-free SiJA72ADP-T1-GE3						
ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless	otherwise no	ted)					
DADAMETED	CAMBOI	LIMIT	LIMIT				

ABSOLUTE MAXIMUM RATINGS	$(T_A = 25 ^{\circ}C, \text{ unless})$	s otherwise noted	d)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	40	V	
Gate-source voltage		V _{GS}	+20, -16	v
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		96	
	T _C = 70 °C	I _D	77	
	T _A = 25 °C	ID D	27.9 ^{b, c}	
	T _A = 70 °C		22.4 ^{b, c}	A
Pulsed drain current (t = 100 μs)		I _{DM}	150	^
Out the second of the design of	T _C = 25 °C		51.7	
Continuous source-drain diode current	T _A = 25 °C	l _s	4.4 b, c	
Single pulse avalanche current L = 0.1 mH		I _{AS}	15	
Single pulse avalanche Energy	L = 0.1 IIII	E _{AS}	11.25	mJ
Maximum power dissipation	T _C = 25 °C		56.8	
	T _C = 70 °C		36.4	w
	T _A = 25 °C	P _D	4.8 b, c	VV
	T _A = 70 °C]	3.1 b, c	
Operating junction and storage temperature rar	T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) d, e			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R _{thJA}	22	26	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.8	2.2	C/VV

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 70 °C/W

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	22	-	1406
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5.4	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	-	2.4	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20, -16 V	-	-	± 100	nA
7		V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	μΑ
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30	-	-	Α
	_	V _{GS} = 10 V, I _D = 10 A	-	0.00285	0.00342	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A	-	0.00398	0.00478	Ω
Forward transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 10 A	-	76	-	S
Dynamic ^b	<u> </u>	30 . 0		l	l	
Input capacitance	C _{iss}		-	2530	-	
Output capacitance	Coss		_	465	-	pF
Reverse transfer capacitance	C _{rss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	19	-	
C _{rss} /C _{iss} ratio			_	0.0075	0.0150	
		V _{DS} = 20 V, V _{GS} = 10 V, I _D = 26 A	-	33	50	
Total gate charge	Q_g		-	14.8	23	nC
Gate-source charge	Q _{as}	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 26 \text{ A}$	_	8.2	-	
Gate-drain charge	Q _{qd}		_	2.3	-	
Output charge	Q _{oss}	V _{DS} = 20 V, V _{GS} = 0 V	-	17.6	27	
Gate resistance	Rq	f = 1 MHz	0.26	1.3	2.6	Ω
Turn-on delay time	t _{d(on)}		-	15	30	
Rise time	t _r	$V_{DD} = 20 \text{ V}, R_{I} = 1 \Omega$	_	7	14	-
Turn-off delay time	t _{d(off)}	$I_D \cong 20.8 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	_	35	70	
Fall time	t _f		_	5	10	
Turn-on delay time	t _{d(on)}		-	30	60	ns
Rise time	t _r	$V_{DD} = 20 \text{ V}, R_1 = 1 \Omega$	_	150	300	- - -
Turn-off delay time	t _{d(off)}	$I_D \cong 20.8 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	35	70	
Fall time	t _f		-	14	28	
Drain-Source Body Diode Characteristic	:s			L	l I	
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	51.7	
Pulse diode forward current ($t_p = 100 \mu s$)	I _{SM}	-	-	-	150	Α
Body diode voltage	V _{SD}	I _S = 10 A	-	0.74	1.1	V
Body diode reverse recovery time	t _{rr}	<u> </u>	-	22	44	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 20.8 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	_	10	20	nC
Reverse recovery Fall time	t _a	$T_J = 25 \text{ °C}$	_	12	-	
Reverse recovery rise time	t _b		_	10	_	ns

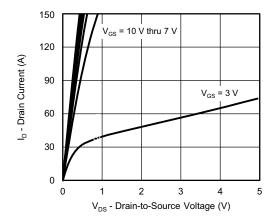
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

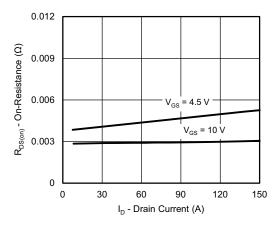
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



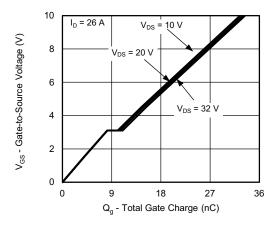
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



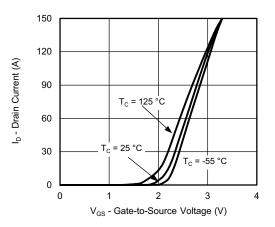
Output Characteristics



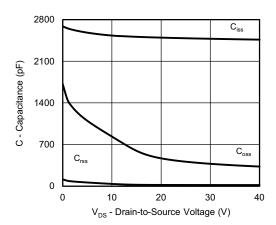
On-Resistance vs. Drain Current



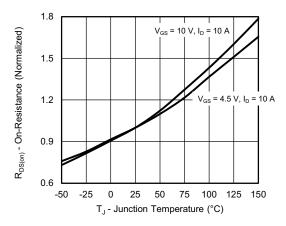
Gate Charge



Transfer Characteristics



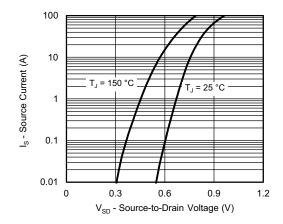
Capacitance



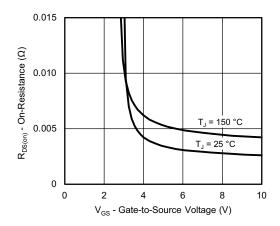
On-Resistance vs. Junction Temperature



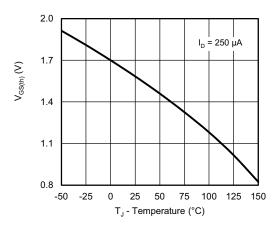
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



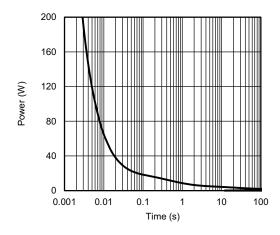
Source-Drain Diode Forward Voltage



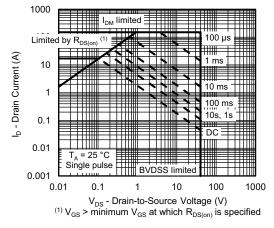
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



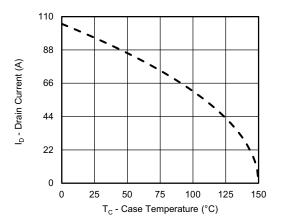
Single Pulse Power, Junction-to-Ambient



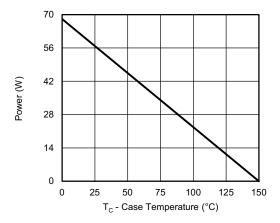
Safe Operating Area

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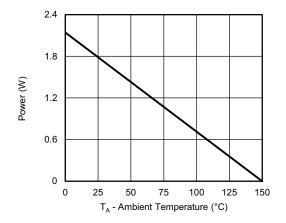
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating a







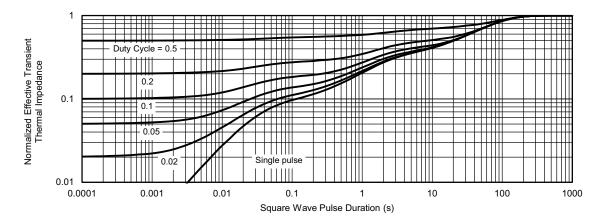
Power, Junction-to-Ambient

Note

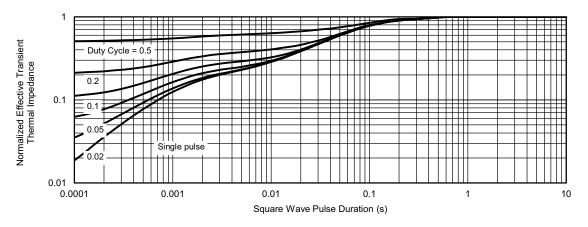
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75342.



PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23		0.009			
W1		0.41			0.016		
W2		2.82			0.111		
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. E, 05-Aug-2019

DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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